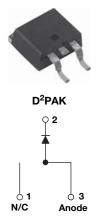
Vishay Semiconductors

## HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 4 A



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PRODUCT SUMMARY							
Package	TO-263AB (D <sup>2</sup> PAK)						
I <sub>F(AV)</sub>	4 A						
V <sub>R</sub>	600 V						
V <sub>F</sub> at I <sub>F</sub>	1.8 V						
t <sub>rr</sub> (typ.)	17 ns						
T <sub>J</sub> max.	150 °C						
Diode variation	Single die						

#### FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low  $\mathsf{I}_{\mathsf{RRM}}$
- $\bullet$  Very low  $\mathsf{Q}_{\mathsf{rr}}$
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
   FREE
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

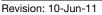
#### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the  $t_b$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V <sub>R</sub>		600	V			
Maximum continuous forward current	١ <sub>F</sub>	T <sub>C</sub> = 100 °C	4				
Single pulse forward current	I <sub>FSM</sub>		25	А			
Maximum repetitive forward current	I <sub>FRM</sub>		16				
Maximum namer dissinction	P <sub>D</sub>	T <sub>C</sub> = 25 °C	25	W			
Maximum power dissipation		T <sub>C</sub> = 100 °C	10	vv			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C			



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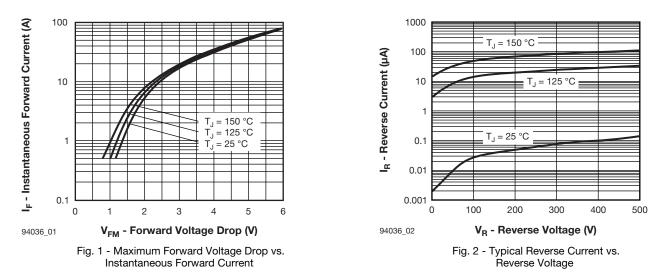
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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-		
		I <sub>F</sub> = 4.0 A		-	1.5	1.8	v	
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2		
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7		
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	See fig. 0	-	0.17	3.0		
leakage current	I <sub>RM</sub>	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	44	300	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from pa	Measured lead to lead 5 mm from package body - 8.0 -					

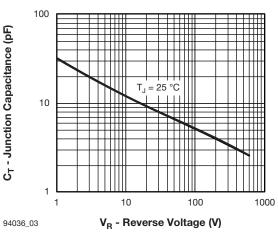
DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS				UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}$	√μs, V <sub>R</sub> = 30 V	-	17	-			
Reverse recovery time See fig. 5, 6	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	28	42	ns		
000 lig. 5, 0	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A nC		
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60			
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105			
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A/µs		
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	Λµs		

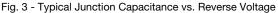
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0	K/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	N/¥¥		
Weight			-	2.0	-	g		
vveigni			-	0.07	-	oz.		
Marking device		Case style D <sup>2</sup> PAK		HFA04	TB60S			

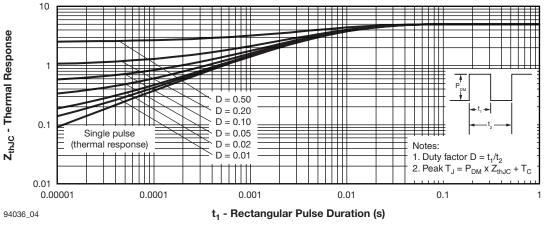
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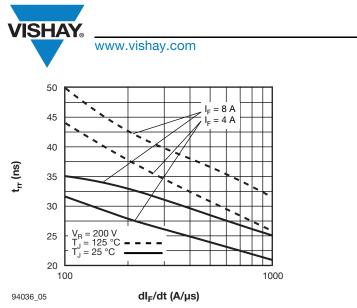


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

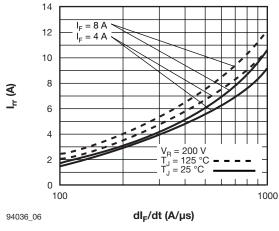


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

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VS-HFA04TB60SPbF

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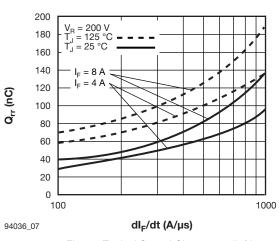


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

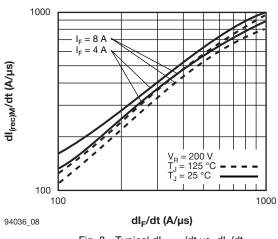


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt



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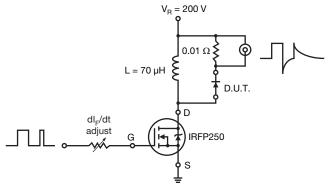


Fig. 9 - Reverse Recovery Parameter Test Circuit

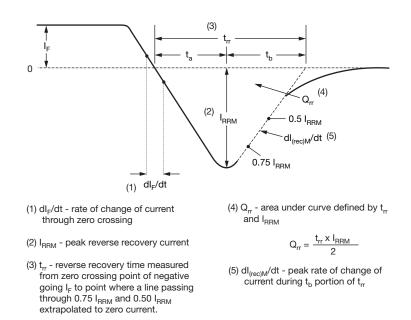


Fig. 10 - Reverse Recovery Waveform and Definitions

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#### Vishay Semiconductors

#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	04	тв	60	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	<ol> <li>HPP product suffix</li> <li>HEXFRED<sup>®</sup> family</li> </ol>								
	3 - Process designator: A = Electron irradiated								
	4 -	Cur	rent rati	ng (04 =	= 4 A)				
	5 -	Pac	kage ou	utline (TI	B = TO-	220, 2 I	eads)		
	6 -	Volt	tage rati	ng (60 =	= 600 V)				
	7 -	S =	D <sup>2</sup> PAK						
	8 - • None = Tube (50 pieces)								
	<ul> <li>TRL = Tape and reel (left oriented)</li> </ul>								
	<ul> <li>TRR = Tape and reel (right oriented)</li> </ul>								
	9 -	PbF	= Lead	l (Pb)-fre	ee				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



## **Outline Dimensions**

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D<sup>2</sup>PAK



Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220) в Pad layout (2)(3) A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (0.38)<sup>MIN.</sup> (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.01 MIN. Ľ <u>L2</u> Ĥ ţ В В 2.32 MIN. -(0.08) 2.64 (0.103) 2.41 (0.096) (3)Ċ 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 4 A1 Lead tip (b, b2)-Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode Rotated 90 °CW

Scale: 8:1

#### **DIMENSIONS** in millimeters and inches

SYMBOL	MILLIMETERS		INCHES		NOTES
STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC 0.100 BS0		BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

 $^{(1)}\,$  Dimensioning and tolerancing per ASME Y14.5 M-1994  $\,$ 

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

 $^{(3)}\,$  Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC outline TO-263AB

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